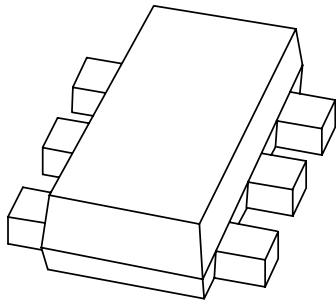


DATA SHEET



PMEG2015EV

Low V_F MEGA Schottky barrier diode

Product specification
Supersedes data of 2003 May 21

2003 Jun 03

Low V_F MEGA Schottky barrier diode

PMEG2015EV

FEATURES

- Forward current: 1.5 A
- Reverse voltage: 20 V
- Very low forward voltage
- Ultra small plastic SMD package
- Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

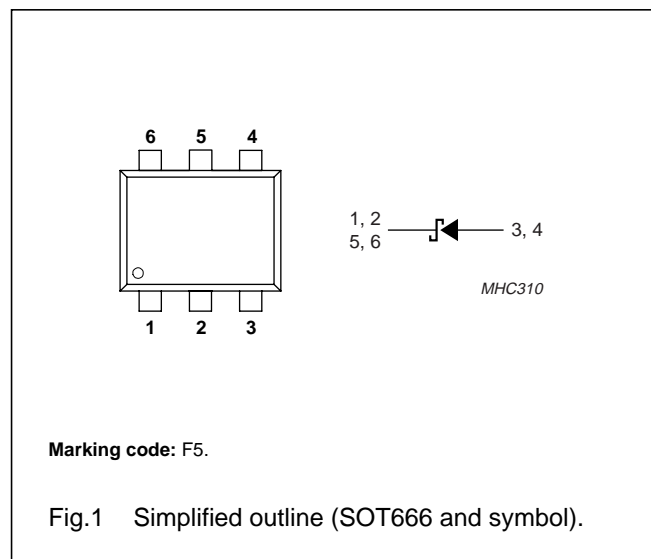
- Low voltage rectification
- High efficiency DC-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	cathode
3	anode
4	anode
5	cathode
6	cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current	$T_s < 55\text{ °C}$	–	1.5	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$ square wave; note 1	–	10	A
I_{FRM}	repetitive peak forward current	$t_p = 1\text{ ms}$; $\delta = \leq 0.25$	–	4.5	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+125	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	continuous forward voltage	see Fig.2; note 1			
		$I_F = 10\text{ mA}$	240	270	mV
		$I_F = 100\text{ mA}$	300	350	mV
		$I_F = 1000\text{ mA}$	480	550	mV
I_R	continuous reverse current	see Fig.3; note 2			
		$V_R = 5\text{ V}$	5	10	μA
		$V_R = 8\text{ V}$	7	20	μA
		$V_R = 15\text{ V}$	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	19	25	pF

Notes

1. Only valid if pins 1, 2 and 5, 6 are soldered on 1 cm^2 copper solder land.
2. Pulse test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W
$R_{th\ j-s}$	thermal resistance from junction to solder point	note 3	80	K/W

Notes

1. Refer to SOT666 standard mounting conditions.
2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm^2 .
3. Soldering point of cathode tabs.

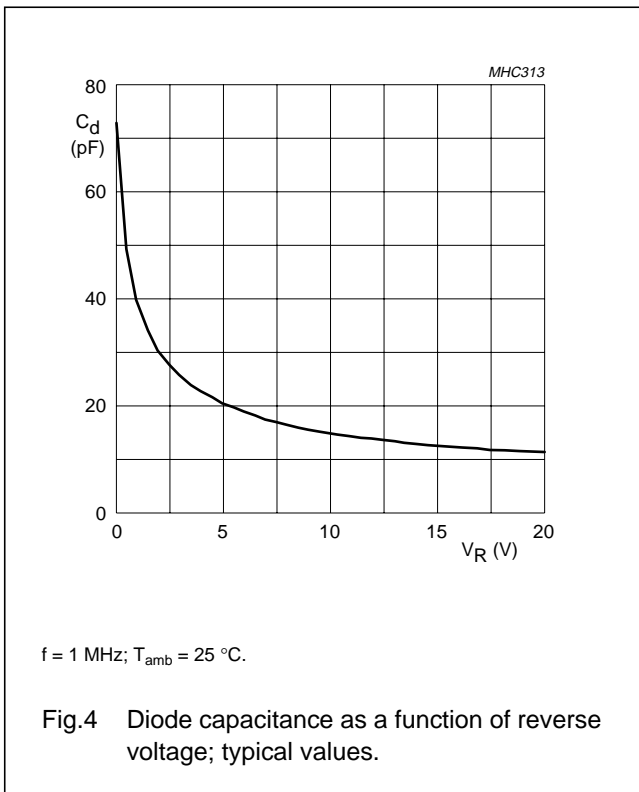
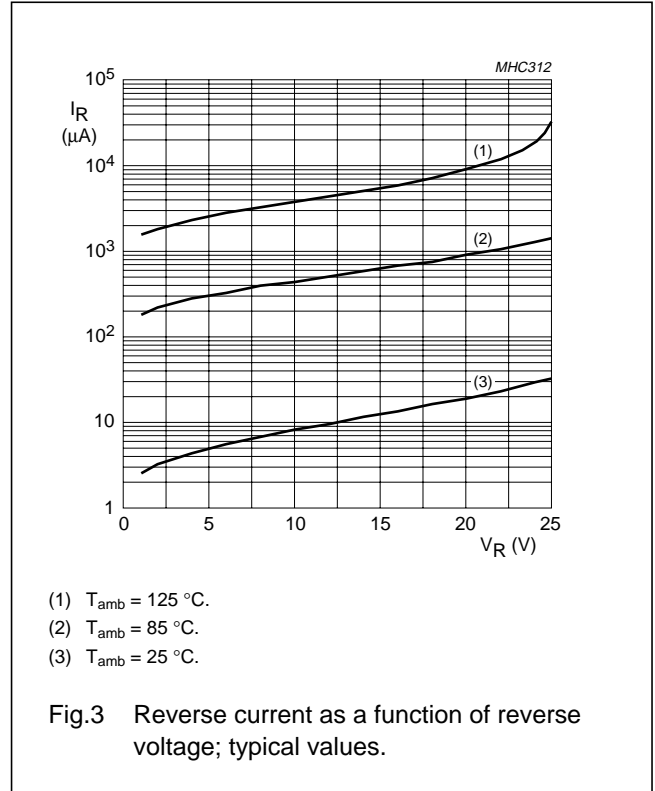
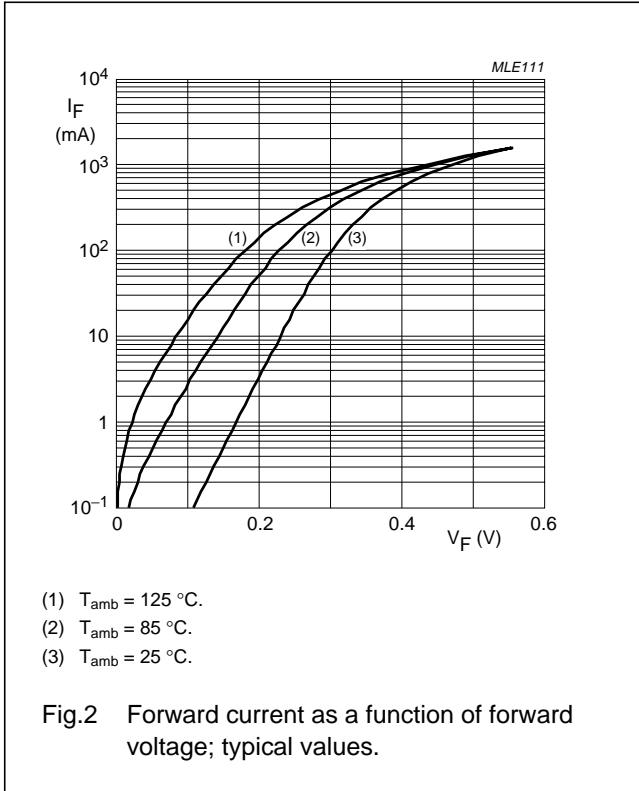
Soldering

Reflow soldering is the only recommended soldering method.

Low V_F MEGA Schottky barrier diode

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GRAPHICAL DATA



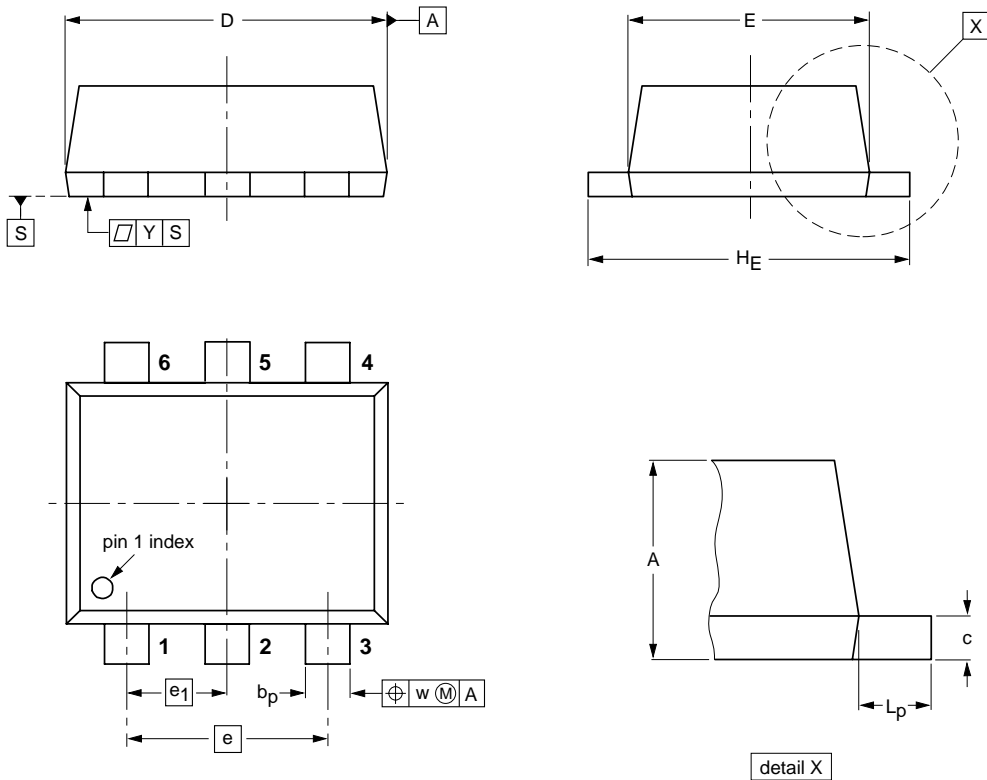
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT666					01-01-04 01-08-27

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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